Dynamics of Sn adatoms at the single steps on the Si(111)- $\sqrt{3}\times\sqrt{3}$ -Sn surface

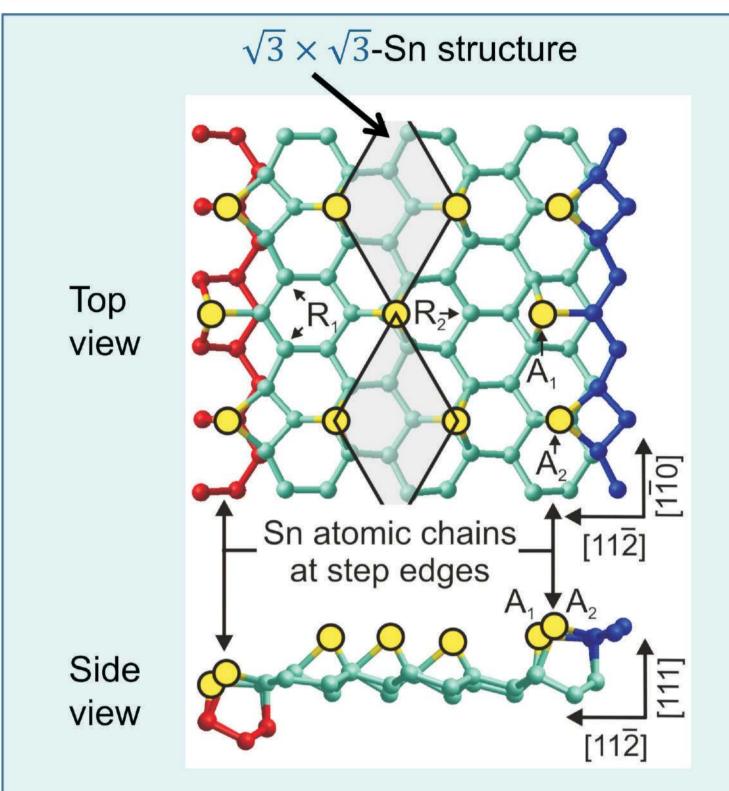
R. Zhachuk, D. Rogilo, A. Petrov, D. Sheglov, A. Latyshev, S. Colonna, F.Ronci Institute of Semiconductor Physics, pr. Lavrentyeva 13, Novosibirsk 630090, Russia CNR-Instituto di Struttura della Materia, via del Fosso del Cavaliere 100, I-00133 Roma, Italy

Atomic structure of a single step

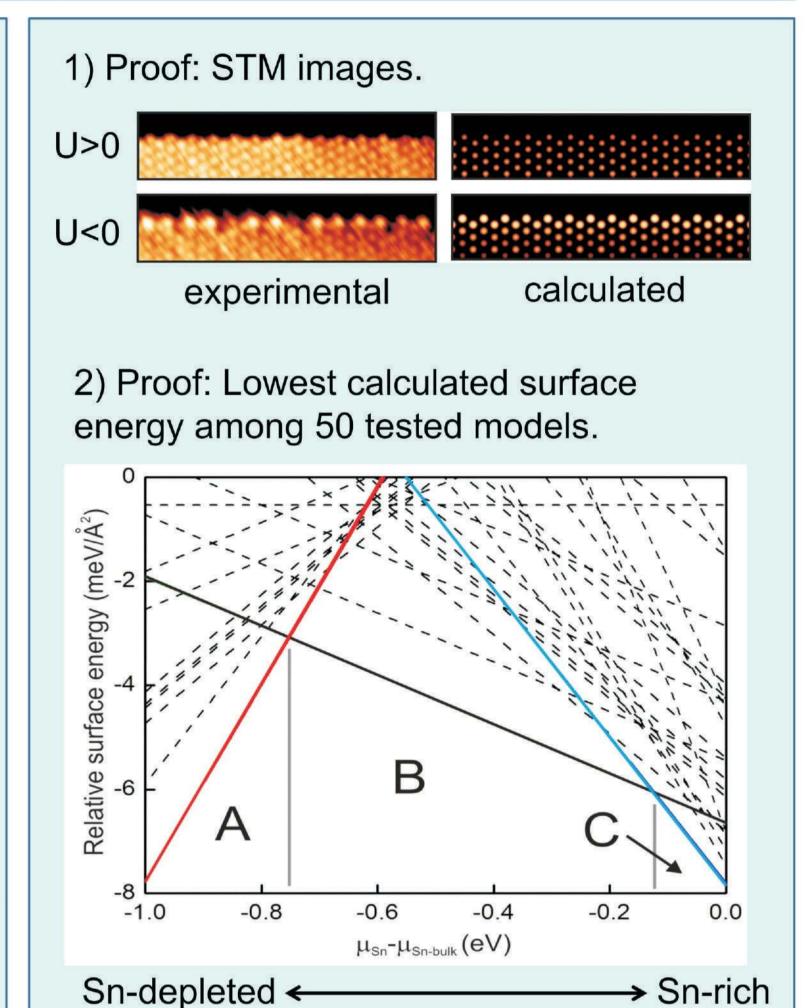
Methods: low-temperature scanning tunneling microscopy (LT-STM, Omicron), density functional theory calculations (SIESTA) using generalized gradient approximation (GGA).

References:

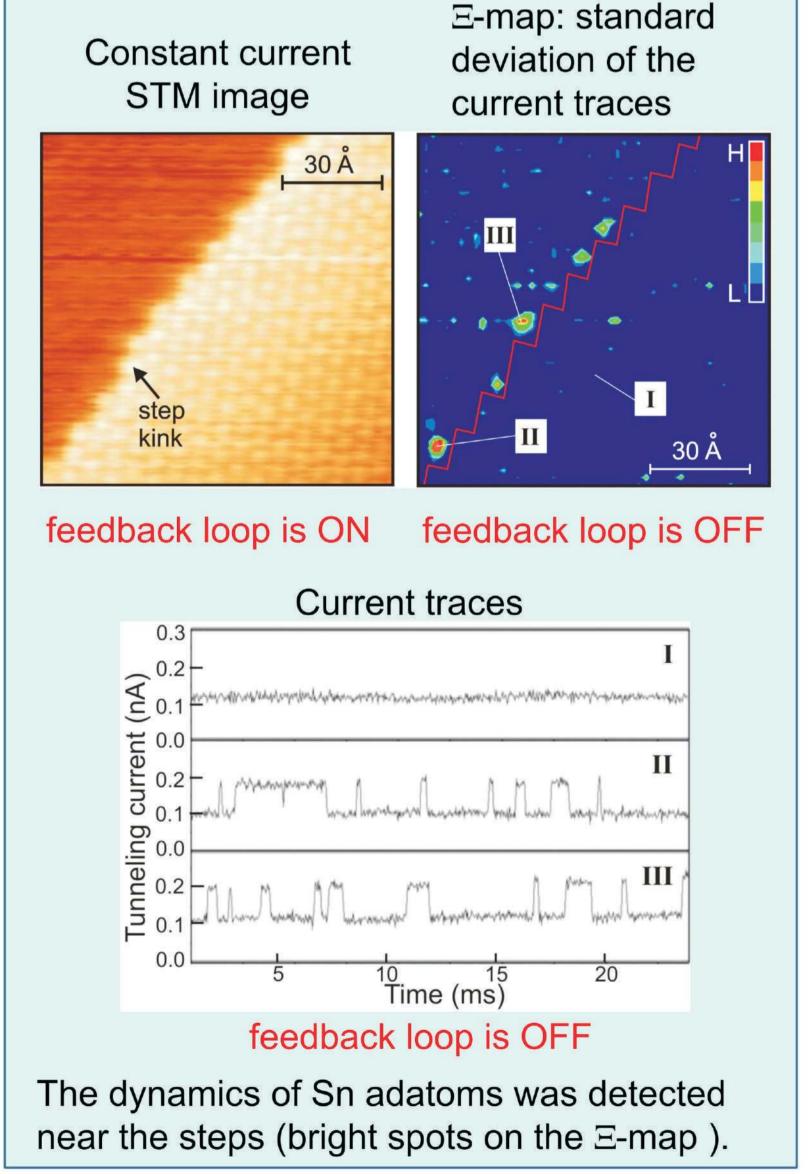
- 1. R. A. Zhachuk at al., Phys. Rev. B 104 (2021) 125437
- 2. F. Ronci et al., Phys. Rev. Lett. 95 (2005) 156101.
- 3. F. Ronci et al., Phys. Rev. Lett. 99 (2007) 166103.
- 4. F. Ronci et al., J. Phys.: Condens. Matter 22 (2010) 264003.

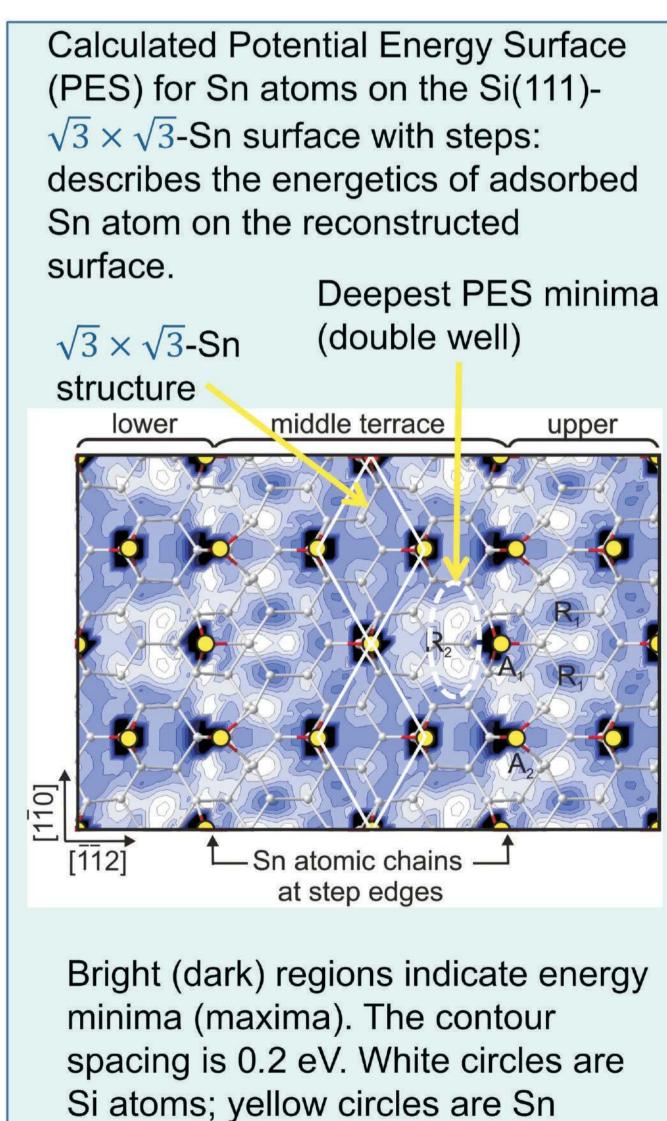


Model "B". Yellow balls – Sn atoms, R_1 , R_2 – rest atoms, A_1 , A_2 – Sn adatoms forming Sn chains along step edges, red, cyan and blue balls are Si atoms of the lower, middle and upper (111) terraces, respectively.

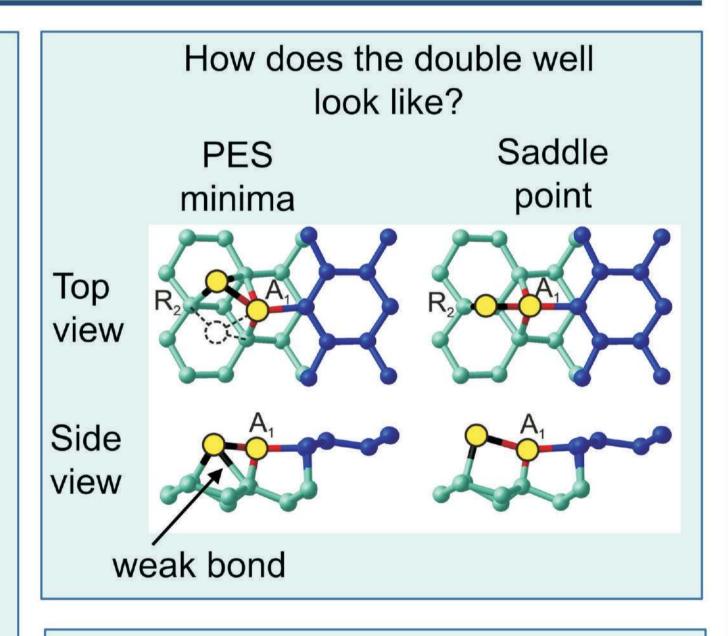


Dynamics of Sn adatoms at T=80 K





atoms.



Conclusions:

- 1) Step atomic structure is determined.
- 2) Dynamics of Sn adatoms near step edges is explained by formation of double wells.

